

# STTH112

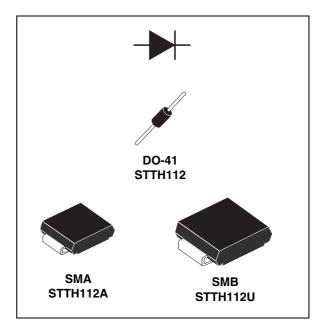
## High voltage ultrafast rectifier

### Features

- Low forwarded voltage drop
- High reliability
- High surge current capability
- Soft switching for reduced EMI disturbances
- Planar technology

### Description

The STTH112, which is using ST ultrafast high voltage planar technology, is specially suited for free-wheeling, clamping, snubbering, demagnetization in power supplies and other power switching applications



### Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	1 A
V <sub>RRM</sub>	1200 V
T <sub>j (max)</sub>	175 °C
V <sub>F (max)</sub>	1.65 V

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## **1** Electrical characteristics

### Absolute ratings (limiting values)

Symbol	Parameter		Value	Unit		
V <sub>RRM</sub>	Repetitive peak reverse voltage				1200	V
V <sub>(RMS)</sub>	Voltage rms				850	V
		TI = 85°C	δ =0.5	DO-41		
I <sub>F(AV)</sub> Average fo	Average forward current	TI = 115°C	δ=0.5	SMA	1	А
	TI = 125°C			SMB		
				DO-41	20	
I <sub>FSM</sub>	I <sub>FSM</sub> Forward surge current t = 8.3 ms			SMA	10	А
				SMB	18	
T <sub>stg</sub>	Storage temperature range					°C
Тj	Maximum operating junction temperature				+ 175	°C

### Table 2.Thermal parameters

Symbol	Parameter			Value	Unit
		L = 10 mm	DO-41	45	
R <sub>th (j-l)</sub>	Junction to lead		SMA	30	°C/M
			SMB	25	°C/W
R <sub>th (j-a)</sub>	Junction to ambient	L = 10 mm	DO-41	110	

### Table 3. Static electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
	Povorso lookago ourront	V <sub>R</sub> = 1200 V	T <sub>j</sub> = 25 °C			5	
'R	I <sub>R</sub> Reverse leakage current V <sub>R</sub>	v <sub>R</sub> = 1200 v	T <sub>j</sub> = 125 °C			50	μA
			T <sub>j</sub> = 25 °C			1.9	
V <sub>F</sub> Forward voltage drop	Forward voltage drop	I <sub>F</sub> = 1 A	T <sub>j</sub> = 125 °C		1.17	1.65	V
			T <sub>j</sub> = 150 °C		1.10	1.55	

### Table 4. Dynamic electrical characteristics

Symbol	Parameter	Tests conditions		Min.	Тур.	Max.	Unit
t <sub>rr</sub>	Reverse recovery time	I <sub>F</sub> = 0.5 A I <sub>rr</sub> = 0.25 A I <sub>R</sub> = 1A	T <sub>j</sub> = 25 °C			75	ns
t <sub>fr</sub>	Forward recovery time	$I_F = 1 A$	T 05.00			500	ns
V <sub>FP</sub>	Forward recovery voltage	dl <sub>F</sub> /dt = 50 A/µs V <sub>FR</sub> = 1.1 x V <sub>Fmax</sub>	T <sub>j</sub> = 25 °C			30	V



1.0

0.9

0.8

0.7

0.6

0.5

0.4

0.3

0.2

0.1

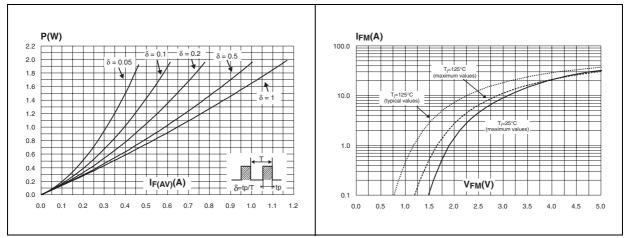
0.0

57

1.E-01

# Figure 1. Conduction losses versus average Figure 2. current





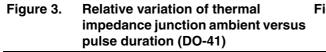


Figure 4. Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4) (SMA)

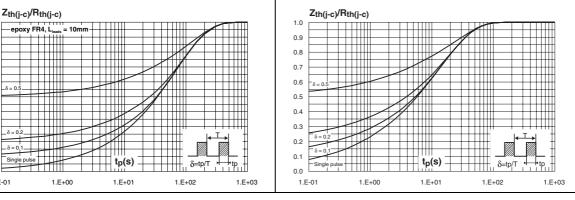
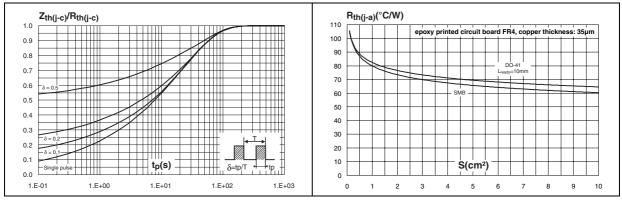


Figure 5. Relative variation of thermal impedance junction ambient versus pulse duration (epoxy FR4)(SMB)

Figure 6. Thermal resistance junction to ambient versus copper surface under each lead (DO-41, SMB)



# Figure 7. Thermal resistance junction to ambient versus copper surface under each lead (epoxy printed circuit board FR4, copper thickness: 35µm) (SMA)

	R <sub>th(j-a)</sub> (°C/W)
140	
130	
120	
110	
100	
90	
80	SINIA SINIA
70 60	
50	
40 30	
20	
10	
0	
	0.0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0

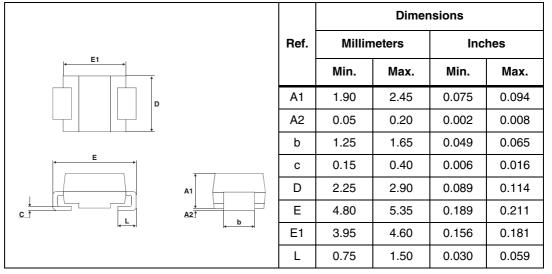


## 2 Package information

- Epoxy meets UL 94, V0
- Band indicates cathode
- Bending method (DO-41): see Application note AN1471

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <u>www.st.com</u>. ECOPACK<sup>®</sup> is an ST trademark.

Table 5. SMA dimensions



#### Figure 8. Footprint (dimensions in mm)

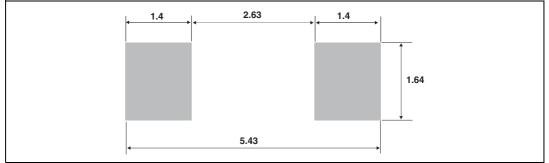
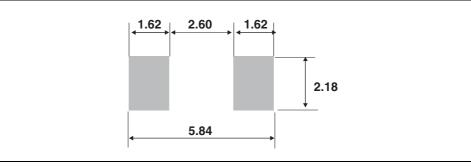




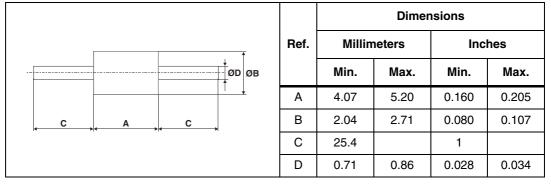
Table 6.SMB dimensions

				Dimer	nsions		
E1		Ref.	Millim	Millimeters		Inches	
			Min.	Max.	Min.	Max.	
		A1	1.90	2.45	0.075	0.096	
	A2	0.05	0.20	0.002	0.008		
		b	1.95	2.20	0.077	0.087	
	С	0.15	0.40	0.006	0.016		
	A1	D	3.30	3.95	0.130	0.156	
		Е	5.10	5.60	0.201	0.220	
	l <b>∢</b> →	E1	4.05	4.60	0.159	0.181	
		L	0.75	1.50	0.030	0.059	

### Figure 9. Footprint (dimensions in mm)



### Table 7. DO-41 (plastic) dimensions



# **3** Ordering information

### Table 8. Ordering information

Order code	Marking	Package	Weight Base qty De		Delivery Mode
STTH112	STTH112	DO-41	0.34 g	2000	Ammopack
STTH112A	H12	SMA	0.068 g	5000	Tape and reel
STTH112U	U12	SMB	0.11 g	2500	Tape and reel
STTH112RL	STTH112	DO-41	0.34 g	5000	Tape and reel

## 4 Revision history

Date	Revision Changes		
Jan-2003	2	Initial release.	
22-Jun-2005	3	New value of $T_j = 150$ °C added to table 2. Dimensions A1 E and D updated in Table 4. Data sheet reformatted. No other technical changes.	
20-Mar-2007	4	Reformatted to current standards. Updated dimensions and footprints for SMA and SMB packages.	
30-Sep-2009	5	Updated table 7 package dimensions.	

### Table 9. Document revision history



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